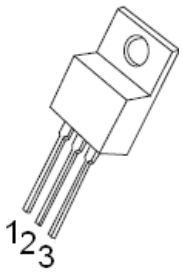
JIANGSU CHANGJIANG ELECTRONICS TECHNOLOGY CO., LTD

TO-220 Plastic-Encapsulate Transistors

2SD1762 TRANSISTOR (NPN)

TO – 220

1. BASE
2. COLLECTOR
3. EMITTER



FEATURES

- Low $V_{CE(sat)}$
- Complements the 2SB1185

MAXIMUM RATINGS (T_a=25℃ unless otherwise noted)

Symbol	Parameter	Value	Unit
V_{CBO}	Collector-Base Voltage	60	V
V_{CEO}	Collector-Emitter Voltage	50	V
V_{EBO}	Emitter-Base Voltage	5	V
I_C	Collector Current	3	A
P_C	Collector Power Dissipation	1	W
$R_{\theta JA}$	Thermal Resistance From Junction To Ambient	125	℃/W
T_j	Junction Temperature	150	℃
T_{stg}	Storage Temperature	-55~+150	℃

ELECTRICAL CHARACTERISTICS (T_a=25℃ unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	I_C=50μA,I_E=0	60			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	I_C=1mA,I_B=0	50			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	I_E=50μA,I_C=0	5			V
Collector cut-off current	I_{CBO}	V_{CB}=40V,I_E=0			1	μA
Emitter cut-off current	I_{EBO}	V_{EB}=4V,I_C=0			1	μA
DC current gain	h_{FE}*	V_{CE}=3V, I_C=0.5A	60		320	
Collector-emitter saturation voltage	$V_{CE(sat)}$*	I_C=2A,I_B=0.2A			1	V
Collector output capacitance	C_{ob}	V_{CB}=10V,I_E=0, f=1MHz		40		pF
Transition frequency	f_T*	V_{CE}=5V,I_C=0.5A, f=30MHz		90		MHz

*Pulse test

CLASSIFICATION OF h_{FE}

RANK	D	E	F
RANGE	60-120	100-200	160-320